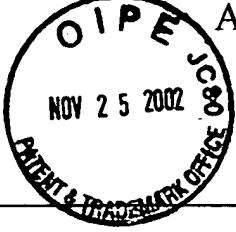


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INFORMATION DISCLOSURE CITATION IN AN APPLICATION  (PTO-1449)		ATTY. DOCKET NO. 49657-961	SERIAL NO. 09/769,496
		APPLICANT Kenji ITOGA, et al.	RECEIVED DEC -2 2002 800 MAIL ROOM
		FILING DATE January 26, 2001	GROUP 2882

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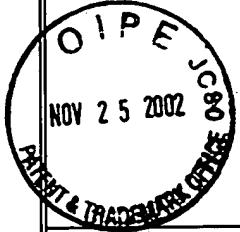
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

"X-Ray nanolithography-the clearest path to 0.1 and sub-0.1um ULSI", M.L. Schattengurg et al , JJAP Series 5, Proc. of 1990 Intern. MicroProcess Conference, pp. 63-70.
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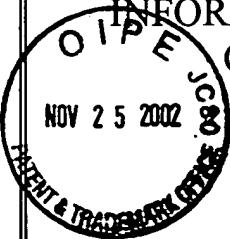
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			APPLICANT Kenji ITOGA, et al.	<i>RECEIVED NOV 25 2002 U.S. PATENT AND TRADEMARK OFFICE 800 MAIL ROOM</i>			
			FILING DATE January 26, 2001	GROUP 2882			
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(PTO-1449)

ATTY. DOCKET NO.
49657-961

SERIAL NO.
09/769,490

APPLICANT
Kenji ITOGA, et al.

FILING DATE
January 26, 2001

GROUP
2882

U.S. PATENT DOCUMENTS

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						Yes	No

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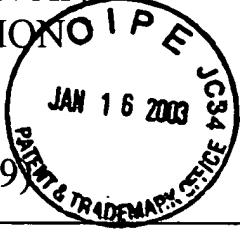
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	<p>"Updated system model for x-ray lithography", M. Khan, L. Mohammad, J. Xiao, L. Ocola, and F. Cerrina, J. Vac. Sci. Technol. B 12(6), Nov/Dec 1994, pp.3930-3935.</p>					
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			APPLICANT Kenji ITOGA, et al.			
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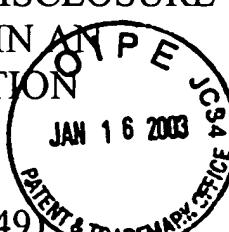
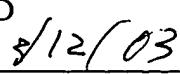
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